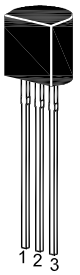
NPN Silicon Epitaxial Planar Transistor
for switching and AF amplifier applications.

2SC828 / 828A

These transistors are subdivided into three groups Q, R and S according to their DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



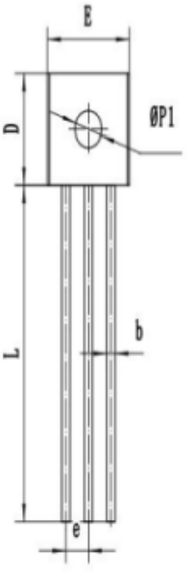
1. Emitter 2. Collector 3. Base
TO-92 Plastic Package

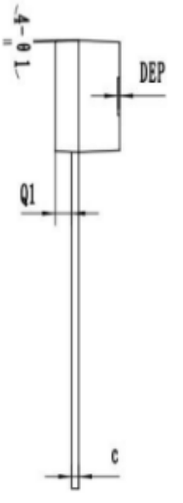
Absolute Maximum Ratings (T_a = 25 °C)

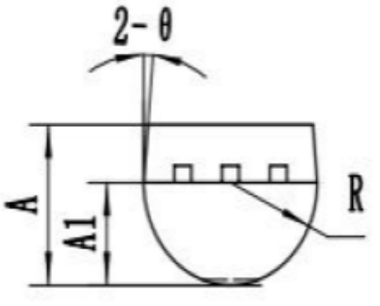
Parameter		Symbol	Value	Unit
Collector Base Voltage	2SC828 2SC828A	V_{CBO}	30 45	V
Collector Emitter Voltage	2SC828 2SC828A	V_{CEO}	25 45	V
Emitter Base Voltage		V_{EBO}	7	V
Collector Current		I_C	50	mA
Peak Collector Current		I_{CM}	100	mA
Power Dissipation		P_{tot}	400	mW
Junction Temperature		T_j	150	°C
Storage Temperature Range		T_{stg}	- 55 to + 150	°C

Characteristics at T_a = 25 °C

Parameter			Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at V_{CE} = 5 V, I_C = 2 mA	Current Gain Group	Q R S	h_{FE} h_{FE} h_{FE}	130 180 260	- - -	280 360 520	- - -
Collector Base Breakdown Voltage at I_C = 10 µA	2SC828 2SC828A		V_{CBO}	30 45	- -	- -	V
Collector Emitter Breakdown Voltage at I_C = 2 mA	2SC828 2SC828A		V_{CEO}	25 45	- -	- -	V
Emitter Base Breakdown Voltage at I_C = 10 µA			V_{EBO}	7	-	-	V
Base Emitter Voltage at I_C = 10 mA, V_{CE} = 5 V			V_{BE}	-	-	0.8	V
Gain Bandwidth Product at I_C = 2 mA, V_{CE} = 10 V			f_T	-	220	-	MHz







SYMBOL	MM		
	MIN	NOM	MAX
*A	3.00	3.25	3.50
A1	2.20	2.30	2.40
*b	0.40	0.45	0.50
*c	0.25	0.30	0.35
*D	4.50	4.60	4.70
*E	4.50	4.60	4.70
*e	1.22	1.27	1.32
*L	14.00	14.30	14.60
R	2.20	2.30	2.40
Q1	0.85	0.90	0.95
θ	3°	5°	7°
Ø1	1°	3°	5°
ØP1	1.40	1.50	1.60
DEP	0.05	0.10	0.20
带*为检验尺寸			